

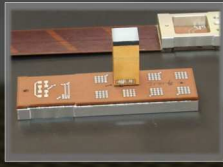
# Imaging X-Ray Detector Front-end with High Dynamic Range: IDeF-X HD

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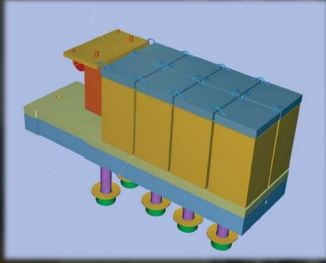
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## OBJECTIVES



MACSI (Modular Assembly of Caliste Spectro-Imager) gamma ray camera module with large focal plane array

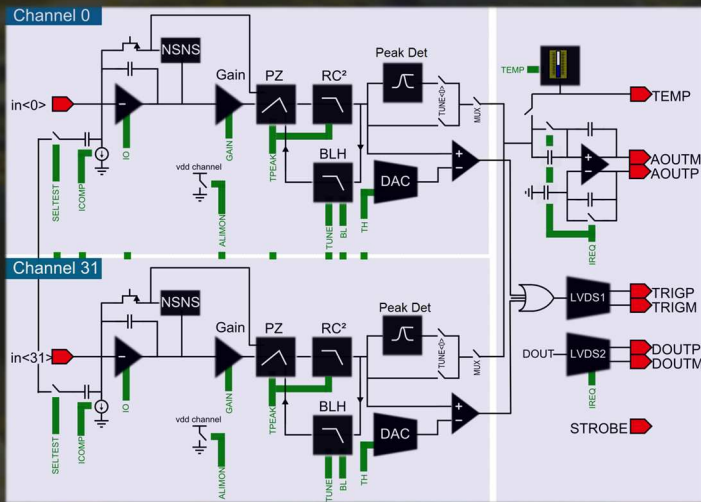
2048 pixels, 8 Caliste 256 modules

IDeF-X HD is designed for MACSI mini gamma-ray camera for spectroscopy in space applications with high spectral resolution (FWHM < 1keV @ 60keV).

Presented ASIC is a new CMOS readout circuit realized in AMS 0.35μm. It is a low noise, low power, 32-channel front-end with self-triggering capability.

The circuit is aimed for readout of pixelated Cd(Zn)Te with 625μm pitch. It is optimized for input capacitance of 2pF and 20pA dark current.

## ASIC DESIGN



Scheme of the chip : each channel includes: continuous reset CSA with variable current, Non stationary noise suppressor (NSNS), pole-zero cancellation stage (PZ), gain stage, shaper (RC<sup>2</sup>), baseline holder (BLH), peak detector, discriminator with individual 6 bits threshold. Many parameters are tunable via serial link : gain (dynamic range), peak time, dark input current ( $I_{LEAK}$ ), discrimination threshold, test mask ...

Three readout modes are achievable : hit channel only, "on demand", all channels.

### Main characteristics of the chip:

Technology	CMOS AMS 0.35μm
Channel	32
Power supply	3.3V
Typical power consumption	26mW (800μW/channel)
Polarity	Anode
Conversion factor	50-200 mV/fC (programmable)
Dynamic range (charge)	225 ke <sup>-</sup> (1 MeV)
Discrimination threshold	90 e <sup>-</sup> → 2.3k e <sup>-</sup>
Peak time	0.7μs → 10.7μs
Temperature sensor	1.5°C at -45..20 °C

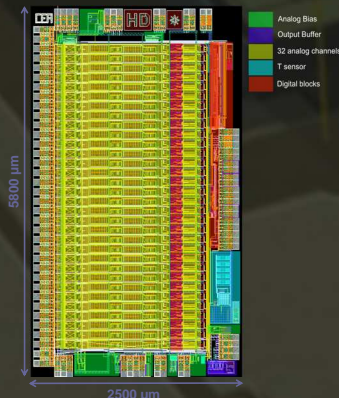


Image of IDeF-X HD SEL hardened design in the standard CMOS AMS 0.35μm technology

## RESULTS

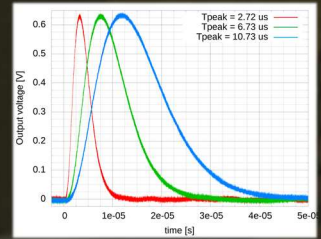
### Functionality

Power consumption:

- ❖ ASIC total: 26mW
- ❖ Per channel: 0.8mW

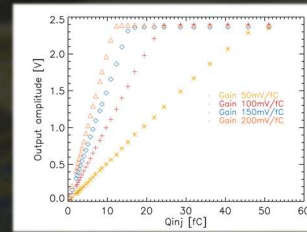
Peak time:

- ❖ The pole zero cancellation stage operates at all peak times
- ❖ Gain constant with peak time
- ❖ No variation of the baseline with  $I_{LEAK}$  0.1pA .. 4nA



Output of the filter stage at different peak times, (gain=200mV/fC,  $I_{LEAK}$ =20pA,  $Q_{in}$ =3.2fC)

### Transfer function

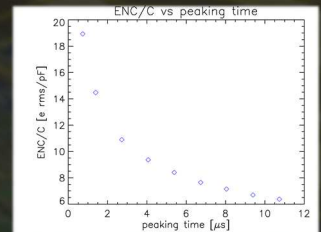
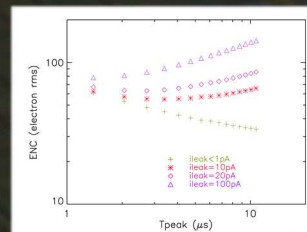


Gain MEASURED [mV/fC]	Dynamic range [fC]	Dynamic range CdTe [eV]	INL [%]
51.8	36	993 k	1.19
102.2	22	607 k	1.39
152.5	13.5	372 k	1.04
203.8	11	303k	1.16

Transfer function ( $I_{LEAK}$ =20pA,  $t_{PEAK}$ =10.7μA, at filter output)

- ❖ Dynamic range up to 1MeV with CdTe

### Equivalent Noise Charge



### Dark current

ENC measurement results at 4 different input currents levels (ileak).

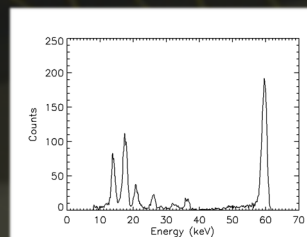
- ❖ ENC min = 33 e<sup>-</sup> rms (750 eV FWHM for CdTe) obtained at the leakage current below 1pA and peak time 10.7μs.

### Input Capacitance

The curves ENC=f(Cin) are fitted to extract the slopes ENC/Cin at different peak times ( $I_{LEAK}$ =20pA). The slope is plotted against the peak time.

- ❖ Minimal slope=6e<sup>-</sup>/pF

### Spectroscopy measurements

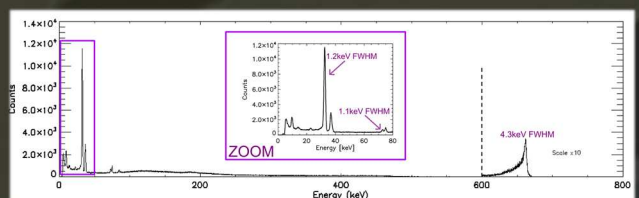


<sup>241</sup>Am

- ❖ 1.01 keV FWHM at 14 keV
- ❖ 1.11 keV FWHM at 60 keV

<sup>137</sup>Cs

- ❖ 4.3 keV FWHM at 662 keV



CdTe schottky 2x2x2mm<sup>3</sup> with Guard Ring, vbias = -1020V, T=-10°C